

### **BS170 / MMBF170**

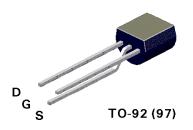
### N-Channel Enhancement Mode Field Effect Transistor

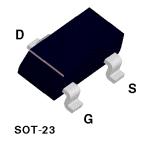
### **General Description**

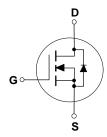
These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

### **Features**

- High density cell design for low R<sub>DS(ON)</sub>.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.







### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units		
V <sub>DSS</sub>	Drain-Source Voltage	60				
$V_{DGR}$	Drain-Gate Voltage ( $R_{GS} \le 1M\Omega$ )	6	60	V		
V <sub>GSS</sub>	Gate-Source Voltage	±	20	V		
I <sub>D</sub>	Drain Current - Continuous	500	500	mA		
	- Pulsed	1200	800			
P <sub>D</sub>	Maximum Power Dissipation	830	300	mW		
	Derate Above 25°C	6.6	2.4	mW/°C		
$T_J$ , $T_{STG}$	Operating and Storage Temperature Range	-55 to 150				
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300				
THERMA	L CHARACTERISTICS					
$R_{\theta^{JA}}$	Thermal Resistacne, Junction-to-Ambient	150	417	°C/W		

Symbol	Parameter	Conditions	Туре	Min	Тур	Max	Units
OFF CHA	RACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 100 \mu\text{A}$	All	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$	All			0.5	μΑ
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 15 \text{ V}, V_{DS} = 0 \text{ V}$	All			10	nA
ON CHAR	ACTERISTICS (Note 1)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	All	0.8	2.1	3	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 200 \text{ mA}$	All		1.2	5	Ω
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 200 \text{ mA}$	BS170		320		mS
		$V_{DS} \ge 2 V_{DS(on)}, I_{D} = 200 \text{ mA}$	MMBF170		320		
DYNAMIC	CHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, \ V_{GS} = 0 \text{ V},$	All		24	40	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz	All		17	30	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		All		7	10	pF
SWITCHIN	IG CHARACTERISTICS (Note 1)						
t <sub>on</sub>	Turn-On Time	$V_{DD} = 25 \text{ V}, \ I_{D} = 200 \text{ m A}, \ V_{GS} = 10 \text{ V}, R_{GEN} = 25 \Omega$	BS170			10	ns
		$V_{DD}$ = 25 V, $I_{D}$ = 500 mA, $V_{GS}$ = 10 V, $R_{GEN}$ = 50 $\Omega$	MMBF170			10	
t <sub>off</sub>	Turn-Off Time	$V_{DD} = 25 \text{ V}, \ I_{D} = 200 \text{ m A}, \ V_{GS} = 10 \text{ V}, \ R_{GEN} = 25 \Omega$	BS170			10	ns
		$V_{DD} = 25 \text{ V}, \ I_{D} = 500 \text{ mA}, \ V_{GS} = 10 \text{ V}, \ R_{GEN} = 50 \ \Omega$	MMBF170			10	

Note:
1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

### **Typical Electrical Characteristics**

### BS170 / MMBF170

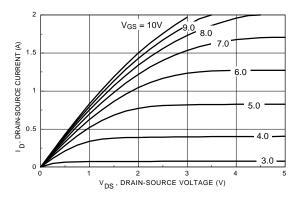


Figure 1. On-Region Characteristics.

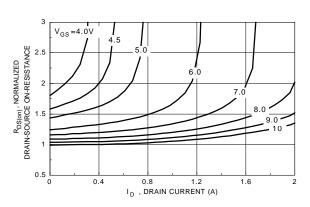


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

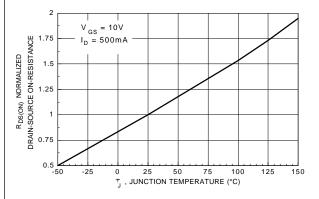


Figure 3. On-Resistance Variation with Temperature.

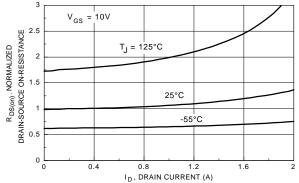


Figure 4. On-Resistance Variation with Drain Current and Temperature.

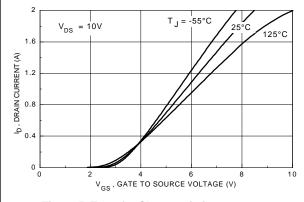


Figure 5. Transfer Characteristics.

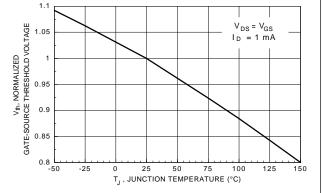


Figure 6. Gate Threshold Variation with Temperature.

### **Typical Electrical Characteristics (continued)**

### BS170 / MMBF170

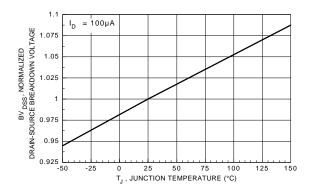


Figure 7. Breakdown Voltage Variation with Temperature.

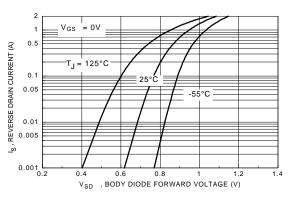


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

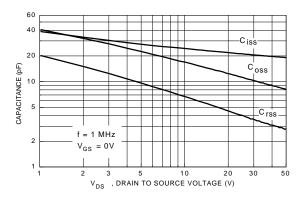


Figure 9. Capacitance Characteristics.

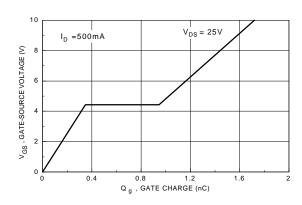


Figure 10. Gate Charge Characteristics.

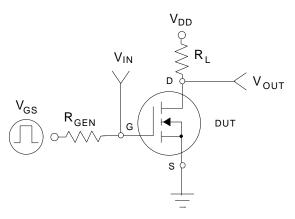


Figure 11. Switching Test Circuit.

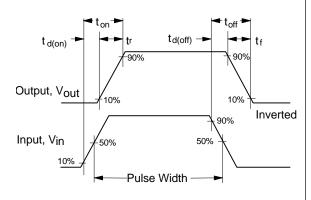


Figure 12. Switching Waveforms.

### Typical Electrical Characteristics (continued)

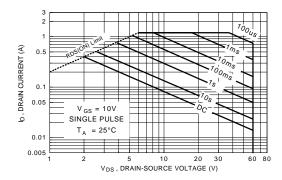


Figure 13. BS170 Maximum Safe Operating Area.

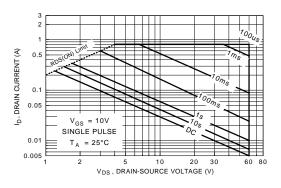


Figure 14. MMBF170 Maximum Safe Operating Area.

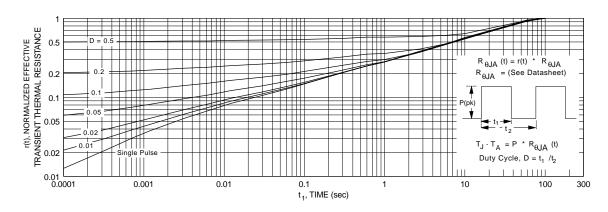


Figure 15. TO-92, BS170 Transient Thermal Response Curve.

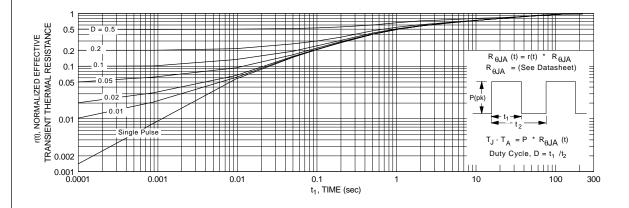


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve.

#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

### TO-92 Tape and Reel Data, continued

### **TO-92 Reeling Style** Configuration: Figure 2.0

### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

### **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM



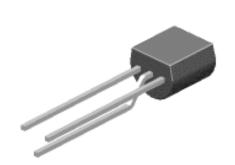
FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

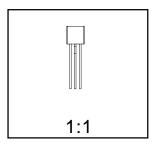


### **TO-92 Package Dimensions**



## TO-92; TO-18 Reverse Lead Form (J35Z Option) (FS PKG Code 92, 94, 96)

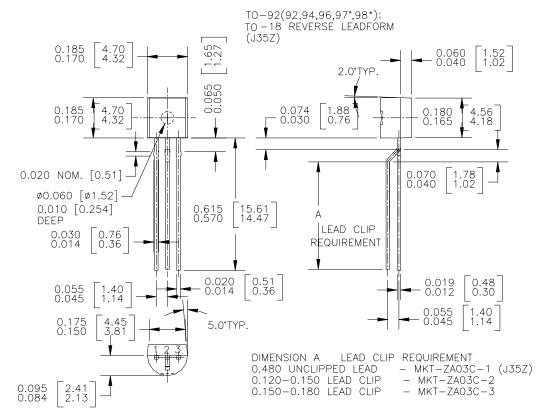




Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.22



**Note:** All package 97 or 98 transistors are leadformed to this configuration prior to bulk shipment. Order L34Z option if in-line leads are preferred on package 97 or 98.

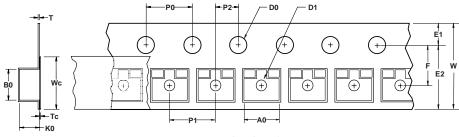
<sup>\*</sup> Standard Option on 97 & 98 package code



### SOT-23 Tape and Reel Data, continued

### **SOT-23 Embossed Carrier Tape**

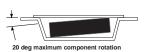
Configuration: Figure 3.0



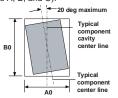
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

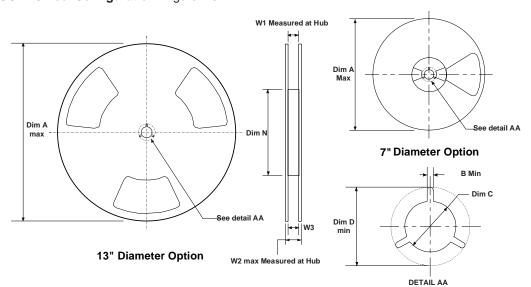


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

### SOT-23 Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



### SOT-23 (FS PKG Code 49)

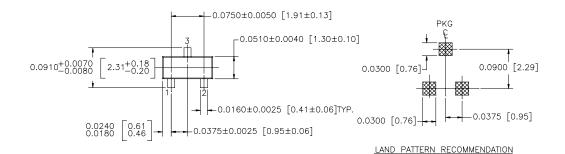


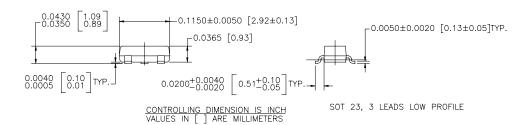


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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DOME™ ISOPLANAR™ Quiet Series™

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Datasheet Identification	Product Status	Definition				
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Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconduct. The datasheet is printed for reference information or				